

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

Sheet

1 of 6

		<i>Complete if Known</i>	
<b>Application No.</b>		10/661,037	
<b>Filing Date</b>		September 12, 2003	
<b>First Named Inventor</b>		John D. Hyde	
<b>Art Unit</b>		2822	
<b>Examiner Name</b>		Ida M. Soward	
<b>Attorney Docket Number</b>		22524-17802	

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Examiner Initials*	Cite No. <sup>1</sup>	Document No.	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
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B1	JP 2005-533372		11-04-2005	Impinj, Inc.	
B2	JP 29-51605		03-10-1998	Programmable Microelectron Co.	
B3	EP 0 562 257 A1		09-29-1993	International Business Machines Corporation	
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B5	WO 00/38239 A1		06-29-2000	Lattice Semiconductor Corporation	

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C1	ANDREOU, AG. et al., "Neural information processing II," in M. Ismail and T. Fiez, eds., Analog VLSI Signal and Information Process, New York: McGraw-Hill, Inc., pp. 358-413, 1994.		
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